Thyristor Surge Protectors

High Voltage Bidirectional

NTVB Series Thyristor Surge Protector Devices (TSPD) protect telecommunication circuits such as central office, access, and customer premises equipment from overvoltage conditions. These are bidirectional devices so they are able to have functionality of 2 devices in one package, saving valuable space on board layout.

These devices will act as a crowbar when overvoltage occurs and will divert the energy away from circuit or device that is being protected.

Use of the NTVB Series in equipment will help meet various regulatory requirements including: GR-1089-CORE, IEC 61000-4-5, ITU K.20/21/45, IEC 60950, TIA-968-A, FCC Part 68, EN 60950, UL 1950.

ELECTRICAL PARAMETERS

	V_{DRM}	V _(BO)	V _T	I _{DRM}	I _(BO)	Ι _Τ	I _H
Device	٧	٧	٧	μΑ	mA	Α	mA
NTVB058NSx-L	58	77	4	5	800	2.2	150
NTVB065NSx-L	65	88	4	5	800	2.2	150
NTVB090NSx-L	90	130	4	5	800	2.2	150
NTVB170Sx-L	170	265	4	5	800	2.2	150
NTVB170NSx-L	170	220	4	5	800	2.2	150
NTVB180Sx-L	170	240	4	5	800	2.2	150
NTVB200Sx-L	200	320	4	5	800	2.2	150
NTVB220NSx-L	220	300	4	5	800	2.2	150
NTVB270Sx-L	270	365	4	5	800	2.2	150
NTVB275NSx-L	275	350	4	5	800	2.2	150
NTVB300Sx-L	300	400	4	5	800	2.2	150

SURGE DATA RATINGS

	Waveform		x = series ratings			
Specification	Voltage μs	Current μs	A	В	С	Unit
GR-1089-CORE	2x10	2x10	150	250	500	A(pk)
TIA-968-A	10x160	10x160	90	150	200	
GR-1089-CORE	10x360	10x360	75	125	175	
TIA-968-A	10x560	10x560	50	100	150	
ITU-T K.20/21	10x700	5x310	75	100	200	
GR-1089-CORE	10x1000	10x1000	50	80	100	

^{*91} Recognized Components



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BIDIRECTIONAL SURFACE MOUNT THYRISTOR 64 – 350 VOLTS





SMB JEDEC DO-214AA CASE 403C

MARKING DIAGRAM



XXXX = Specific Device Code

Y = Year WW = Work Week ■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information on page 4 of this data sheet

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristics (Notes 1, 2, 3)	Symbol	Min	Тур	Max	Unit
Breakover Voltage (Both Polarities) NTVB058NSx-L NTVB065NSx-L NTVB090NSx-L NTVB170Sx-L NTVB170Sx-L NTVB180Sx-L NTVB200Sx-L NTVB220NSx-L NTVB275NSx-L NTVB275NSx-L NTVB300Sx-L	V _(BO)			77 88 130 265 220 240 320 300 365 350 400	V
Off-State Voltage (Both Polarities) NTVB058NSx-L NTVB065NSx-L NTVB090NSx-L NTVB170Sx-L NTVB170Sx-L NTVB180Sx-L NTVB200Sx-L NTVB220NSx-L NTVB275NSx-L NTVB275NSx-L NTVB300Sx-L	V _{DRM}	58 65 90 170 170 200 220 270 275 300			V
Off State Current $(V_{D1} = 50 \text{ V})$ Both Polarities $(V_{D2} = V_{DRM})$ Both Polarities	I _{DRM1} I _{DRM2}			2.0 5.0	μ Α μ Α
Holding Current (Both Polarities) (Note 3) $V_S = 500 \text{ V}$; $I_T = 2.2 \text{ A}$	I _H	150	250	-	mA
On–State Voltage I_T = 1.0 A(pk) (PW = 300 μ Sec, DC = 2%)	V _T	-	-	4.0	V
Maximum Non-Repetitive Rate of Change of On-State Current (Note 1) (Haefely test method, 1.0 pk < 100 A)	di/dt	-	_	500	A/μSec
Critical Rate of Rise of Off–State Voltage (Linear Waveform, V_D = 0.8 V_{DRM} , T_J = 25°C)	dv/dt	5.0	-	-	kV/μSec

CAPACITANCE

			Тур			
Characteristics		Symbol	Α	В	С	Unit
(f=1.0 MHz, 1.0 V _{rms} , 2 Vdc bias)	NTVB058NSx-L NTVB065NSx-L NTVB090NSx-L NTVB170NSx-L NTVB180Sx-L NTVB180Sx-L	Со	84 79 58 39 39	129 123 95 150 59	222 198 154 195 99 97	pF
	NTVB200Sx-L NTVB220NSx-L NTVB270Sx-L NTVB275NSx-L NTVB300Sx-L		36 33 31 28 28	56 52 47 44 44	110 81 76 97 71	

- Electrical parameters are based on pulsed test methods.
 Measured under pulsed conditions to reduce heating
 Allow cooling before testing second polarity.

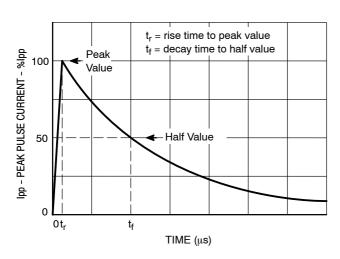
SURGE RATINGS

Characteristics		Α	В	С	Unit
Nominal Pulse Surge Short Circuit Current Non – Repetitive Double Exponential Decay Waveform (Notes 4, 5 and 6) 2 x 10 μSec 10 x 160 μSec 10 x 360 μSec 10 x 560 μSec 10 x 700 μSec 10 x 1000 μSec	IPPS1 IPPS3 IPPS4 IPPS5 IPPS6 IPPS7	150 90 75 50 75 50	250 150 125 100 100 80	500 200 150 150 200 100	A(pk)

- 4. Allow cooling before testing second polarity.5. Measured under pulse conditions to reduce heating.6. Nominal values may not represent the maximum capability of a device.

THERMAL CHARACTERISTICS

Symbol	Rating	Value	Unit
T _{STG}	Storage Temperature Range	-65 to +150	°C
T _J	Operating Temperature Range	-40 to +150	°C
R _{0JA}	Thermal Resistance: Junction-to-Ambient Per EIA/JESD51-3, PCB = FR4 3"x4.5"x0.06" Fan out in a 3x3 inch pattern, 2 oz copper track.	90	°C/W





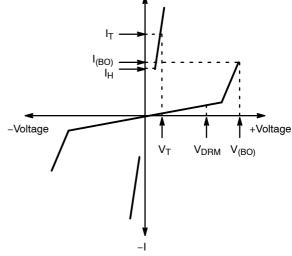


Figure 2. Voltage Current Characteristics of TSPD

Symbol	Parameter
V_{DRM}	Peak Off State Voltage
V _(BO)	Breakover Voltage
I _(BO)	Breakover Current
I _H	Holding Current
V _T	On State Voltage
I _T	On State Current

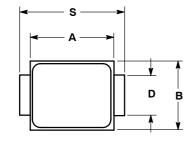
ORDERING INFORMATION

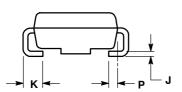
Part Number	Marking	Case	Shipping [†]
NTVB058NSB-L	58NB		
NTVB058NSC-L	58NC		
NTVB065NSA-L	65NA		
NTVB065NSC-L	65NC		
NTVB090NSA-L	90NA		
NTVB170SA-L	170A		
NTVB170SC-L	170C		
NTVB170NSC-L	17NC		
NTVB180SA-L	180A		
NTVB200SA-L	200A	SMB	0500 / Tana and Davi
NTVB200SB-L	200B	(Pb-Free)	2500 / Tape and Reel
NTVB200SC-L	200C		
NTVB220NSC-L	22NC		
NTVB270SA-L	270A		
NTVB270SB-L	270B		
NTVB270SC-L	270C		
NTVB275NSC-L	27NC		
NTVB300SA-L	300A		
NTVB300SB-L	300B		
NTVB300SC-L	300C		

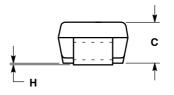
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

SMB CASE 403C-01 **ISSUE A**





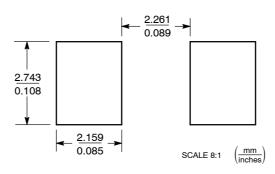


NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
- 3. D DIMENSION SHALL BE MEASURED WITHIN

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.160	0.180	4.06	4.57
В	0.130	0.150	3.30	3.81
С	0.075	0.095	1.90	2.41
D	0.077	0.083	1.96	2.11
Н	0.0020	0.0060	0.051	0.152
J	0.006	0.012	0.15	0.30
K	0.030	0.050	0.76	1.27
P	0.020 REF		0.51	REF
S	0.205	0.220	5.21	5.59

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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